



DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Features

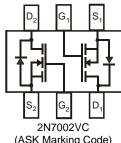
- **Dual N-Channel MOSFET**
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

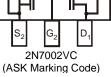
Mechanical Data

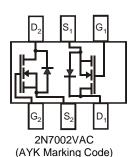
- Case: SOT563
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram (Note 3)
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.003 grams (approximate)











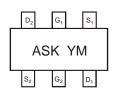
Ordering Information (Note 4)

Part Number	Case	Packaging
2N7002VC-7	SOT563	3000/Tape & Reel
2N7002VAC-7	SOT563	3000/Tape & Reel

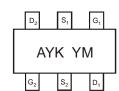
Notes:

- 1. No purposefully added Lead.
- 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com.
- 3. Package is non-polarized. Parts may be on reel in orientation illustrated, 180° rotated, or mixed (both ways).
- 4. For packaging details, go to our website at http://www.diodes.com.

Marking Information



ASK = 2N7002VC Product Type Marking Code (See Note 1) YM = Date Code Marking Y = Year ex: R = 2004 M = Month ex: 9 = September



AYK = 2N7002VAC Product Type Marking Code (See Note 1) YM = Date Code Marking Y = Year ex: R = 2004 M = Month ex: 9 = September

Date Code Key

Year	2004	2005	2006	2007	2008	2009	2010	2011	2012	2013	2014	2015	2016	2017
Code	R	S	Т	U	V	W	Х	Υ	Z	Α	В	С	D	Е
Month	Jan	Feb	Ma	ar .	Apr	May	Jun	Jul	Aug	Se	р	Oct	Nov	Dec
Code	1	2	3		4	5	6	7	8	9		0	N	D



Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Units	
Drain-Source Voltage		V_{DSS}	60	V	
Drain-Gate Voltage $R_{GS} \le 1.0M\Omega$		V_{DGR}	60	V	
Gate-Source Voltage (Note 5)	Continuous Pulsed	V _{GSS}	±20 ±40	V	
Drain Current (Note 5)	Continuous	I_{D}	280	mA	
Drain Current (Note 5)	Pulsed	I _{DM}	1.5	A	

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation	P_{D}	150	mW
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	833	°C/W
Operating and Storage Temperature Range	$T_{J_1}T_{STG}$	-55 to +150	°C

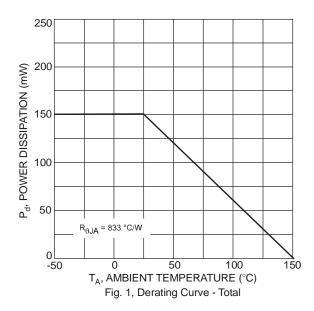
Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteris	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 6)								
Drain-Source Breakdown Voltage		BV _{DSS}	60	70	_	V	$V_{GS} = 0V, I_D = 10\mu A$	
Zero Gate Voltage Drain Current	@ T _C = 25°C @ T _C = 125°C	I _{DSS}			1.0 500	μA	V _{DS} = 60V, V _{GS} = 0V	
Gate-Body Leakage		IGSS		_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTIC (Note 6)					-			
Gate Threshold Voltage		V _{GS(th)}	1.0	_	2.5	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	
Static Drain-Source On-Resistance		R _{DS (ON)}			7.5 13.5	Ω	$V_{GS} = 5V$, $I_D = 0.05A$, $V_{GS} = 10V$, $I_D = 0.5A$, $T_i = 125$ °C	
On-State Drain Current		I _{D(ON)}	0.5	1.0	_	Α	$V_{GS} = 10V, V_{DS} = 7.5V$	
Forward Transconductance		g _{FS}	80	_	_	mS	$V_{DS} = 10V, I_D = 0.2A$	
DYNAMIC CHARACTERISTICS			•		•	•		
Input Capacitance		C _{iss}	_	_	50	pF		
Output Capacitance		Coss	_	_	25	pF	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$	
Reverse Transfer Capacitance		C _{rss}	_	_	5.0	pF		
SWITCHING CHARACTERISTICS								
Turn-On Delay Time		t _{D(ON)}	_	_	20	ns	$V_{DD} = 30V$, $I_D = 0.2A$, $R_L = 150\Omega$,	
Turn-Off Delay Time		t _{D(OFF)}	_		20	ns	$V_{GEN} = 10V$, $R_{GEN} = 25\Omega$	

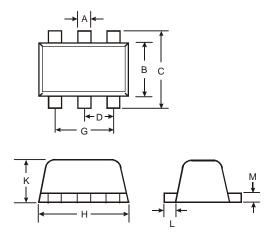
Notes:

^{5.} Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com.
6. Short duration pulse test used to minimize self-heating effect.



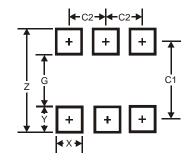


Package Outline Dimensions



SOT563								
Dim	Min	Max	Тур					
Α	0.15	0.30	0.20					
В	1.10	1.25	1.20					
C	1.55	1.70	1.60					
D	-	-	0.50					
G	0.90	1.10	1.00					
Н	1.50	1.70	1.60					
K	0.55	0.60	0.60					
Г	0.10	0.30	0.20					
M	0.10	0.18	0.11					
All Dimensions in mm								

Suggested Pad Layout



Dimensions	Value (in mm)				
Z	2.2				
G	1.2				
Х	0.375				
Y	0.5				
C1	1.7				
C2	0.5				



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